# SI GE

### **Features**

- · Gain control in 20-dB steps
- Very low I/Q amplitude and phase errors
- High input P1dB
- Buffered IF OUT available through baseband output

### **Applications**

- · Infrastructure digital communication systems
- · GSM/cellular transceivers
- ISM band transceivers

Electrostatic sensitive device.

Observe precautions for handling.

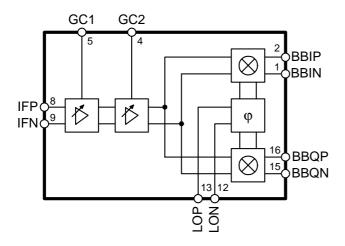


### **Description**

The T0797 is a multi-purpose demodulator RFIC. The silicon monolithic integrated circuit is a designed in Atmels advanced SiGe technology. This demodulator is capable of both quadrature demodulation or direct IF output. Features include switchable gain control on a frequency range from 65 MHz to 300 MHz. The device performs a very low amplitude as well as phase error and allows high input P1dB. The T0797 targets a variety of system applications for communications including 3G wireless.

## **Block Diagram**

Figure 1.





65 - 300 MHz SiGe IF Receiver / Demodulator

T0797

Rev. A2, 03-Dec-01



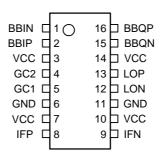


# **Ordering Information**

Extended Type Number	Package	Remarks
T0797	TSSOP16	

# **Pin Configuration**

### Figure 2.



# **Pin Description**

Pin	Symbol	Function			
1	BBIN	Baseband I-axis negative output			
2	BBIP	Baseband I-axis positive output			
3	VCC	5 V power supply			
4	GC2	Gain control input, stage 2			
5	GC1	Gain control input, stage 1			
6	GND	Ground			
7	VCC	5 V power supply			
8	IFP	IF positive input			
9	IFN	IF negative input			
10	VCC	5 V power supply			
11	GND	Ground			
12	LON	Local oscillator, negative input			
13	LOP	Local oscillator, positive input			
14	VCC	5 V power supply			
15	BBQN	Baseband Q-axis negative output			
16	BBQP	Baseband Q-axis positive output			

# **Absolute Maximum Ratings**

All voltages are referred to GND.

Parameter	Symbol	Value	Unit	
Supply voltage	V <sub>CC</sub>	5.5	V	
LO input	LOP, LON	10	dBm	
IF input	IFN, IFP	10	V	
Operating temperature	T <sub>OP</sub>	-40 to +85	°C	
Storage temperature	T <sub>stg</sub>	-65 to +150	°C	

Note: The part may not survive all maximums applied simultaneously

### **Thermal Resistance**

Parameter	Symbol	Value	Unit
Junction ambient	$R_{thJA}$	tbd	K/W

### **Electrical Characteristics**

Test conditions:  $V_{CC}$  = 5 V,  $T_{amb}$  = 25°C, LO input: 0 dBm@200 MHz IF input: @200.1 MHz, GC1 = 0, GC2 = 0; 0 dBm

IF input: @200.1 MHz, GC1 = 0, GC2 = 0; 0 dBm IF input: @200.1 MHz, GC1 = 1, GC2 = 0; -20 dBm IF input: @200.1 MHz, GC1 = 1, GC2 = 1; -40 dBm

No.	Parameters	Test Conditions	Pin	Symbol	Min.	Тур.	Max.	Unit	Type*
1	IF input (I/Q mixing	IF input (I/Q mixing to baseband)							
1.1	Frequency range		8, 9	f	65	120 - 220	300	MHz	В
1.2	Return loss		8, 9	RL		20		dB	D
1.3	Gain	Gain set = high; GC1	8, 9	G		35		dB	Α
1.4	Input P1dB	= GC2 = 1	8, 9	P1dB		-30		dBm	С
1.5	Input IP3		8, 9	IIP3		-20		dBm	В
1.6	Noise figure		8, 9	NF		6		dB	D
1.7	Gain	Gain set = high; GC1	8, 9	G		15		dB	Α
1.8	Input P1dB	= 1; GC2 = 0	8, 9	P1dB		-10		dBm	С
1.9	Input IP3		8, 9	IIP3		0		dBm	В
1.10	Noise figure		8, 9	NF	-3	10		dB	D
1.11	Gain	Gain set = high; GC1	8, 9	G		-5		dB	Α
1.12	Input P1dB	= GC2 = 0	8, 9	P1dB		10		dBm	С
1.13	Input IP3		8, 9	IIP3		20		dBm	В
1.14	Noise figure		8, 9	NF		30		dB	D



### **Electrical Characteristics**

Test conditions:  $V_{CC}$  = 5 V,  $T_{amb}$  = 25°C, LO input: 0 dBm@200 MHz IF input: @200.1 MHz, GC1 = 0, GC2 = 0; 0 dBm

IF input: @200.1 MHz, GC1 = 0, GC2 = 0; 0 dBm IF input: @200.1 MHz, GC1 = 1, GC2 = 0; -20 dBm IF input: @200.1 MHz, GC1 = 1, GC2 = 1; -40 dBm

No.	Parameters	Test Conditions	Pin	Symbol	Min.	Тур.	Max.	Unit	Type*
2	Stuck Mixer (DC to LO port – gain-controlled amplifier)						-11		
2.1	Frequency range		8, 9	f	65	120 - 220	300	MHz	В
2.2	Return loss		8, 9	RL		20		dB	D
2.3	Gain	Gain set = high;	8, 9	G		40		dB	Α
2.4	Input P1dB	GC1 = GC2 = 1	8, 9	P1dB		-26		dBm	С
2.5	Input IP3		8, 9	IIP3		-16		dBm	В
2.6	Noise figure	-	8, 9	NF		6		dB	D
2.7	Gain	Gain set = high;	8, 9	G		20		dB	Α
2.8	Input P1dB	GC1 = 1; GC2 = 0	8, 9	P1dB		-6		dBm	С
2.9	Input IP3	-	8, 9	IIP3		4		dBm	В
2.10	Noise figure	-	8, 9	NF		9		dB	D
2.11	Gain	Gain set = high;	8, 9	G		0		dB	Α
2.12	Input P1dB	GC1 = GC2 = 0	8, 9	P1dB		14		dBm	С
2.13	Input IP3	-	8, 9	IIP3		24		dBm	В
2.14	Noise figure	-	8, 9	NF		30		dB	D
3	I/Q Output				1			I	
3.1	I/Q output frequency range		1, 2, 15, 16	f <sub>I/Q</sub>	DC		500	MHz	D
3.2	I/Q output amplitude error		1, 2, 15, 16		-0.2		+0.2	dB	A
3.3	I/Q phase error		1, 2, 15, 16		-2		+2	deg	А
3.4	I/Q output common mode voltage		1, 2, 15, 16			2.5		V	Α
3.5	I/Q output differential offset voltage		1, 2, 15, 16	V <sub>offset</sub>			10	mV	Α
4	LO input	!	-		+				!
4.1	LO input level		12, 13	P <sub>LO</sub>	-3	0	+3	dBm	D
4.2	Return loss		12, 13	RL <sub>LO</sub>		20		dB	D
5	Miscellaneous	1			1		1	1	1
5.1	Supply voltage		3, 7, 10, 14	$V_{CC}$	4.75	5	5.25	V	А
5.2	Supply current		3, 7, 10, 14	I <sub>CC</sub>		180		mA	Α

# Typical Device Performance

Figure 3. Gain vs. pin high-gain state (11)

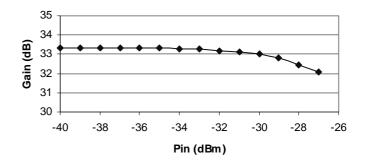


Figure 4. Gain vs. pin low-gain state (00)

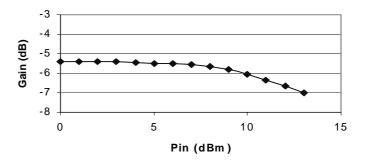
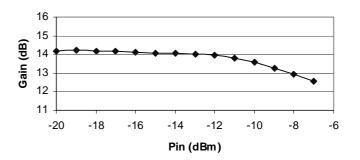


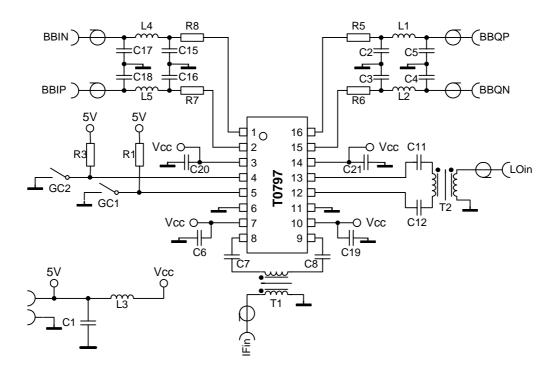
Figure 5. Gain vs. pin medium-gain state (10)





# **Demo Test Board Schematic**

Figure 6.

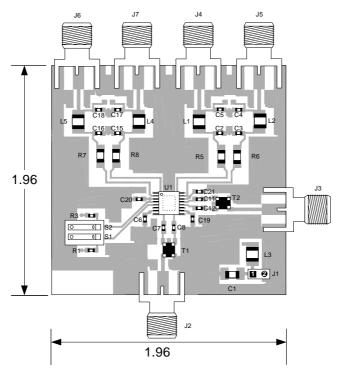


### **Bill of Materials**

Component Designator	Value	Vendor	Part Number	Description
D1		Atmel	T0797	IF receiver
J2, J3, J4, J5, J6, J7		Johnson Components	142-0701-851	SMA end launch connector
T1, T2		Mini-Circuits	TC1-1	Transformer
C1	1uF			1206 size supply bypass capacitor
R1, R3	1 kohm			0603 size
C6, C19, C20, C21	1nF			0603 size
L1, L2, L3, L4, L5	1uH			1210 size
C7, C8, C11, C12	68pF			0603 size
R5, R6, R7, R8	0 Ohm			1206 size
C2, C3, C4, C5, C15, C16, C17, C18	820pF			0603 size

# **Demo Test Board (Fully Asembled PCB)**

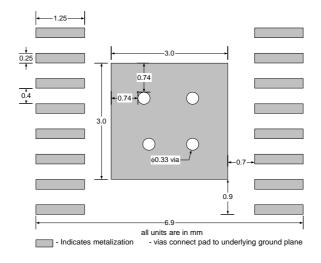
Figure 7.



Note: Dimensions in inches

## **Recommended Package Footprint**

Figure 8.

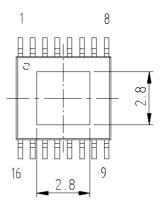


Remark: Heatslug must be soldered to GND



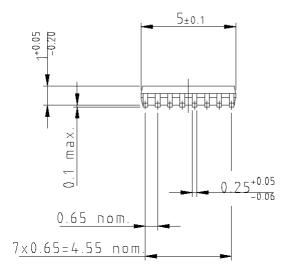


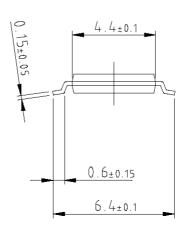
# **Package Information**



Package: SSOP16 (acc. JEDEC SMALL OUTLINE No. MO-153)
Dimensions in mm







## **Ozone Depleting Substances Policy Statement**

It is the policy of Atmel Germany GmbH to

- 1. Meet all present and future national and international statutory requirements.
- 2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

**Atmel Germany GmbH** has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

- 1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
- Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
- 3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

**Atmel Germany GmbH** can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.





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